70V3319/99S

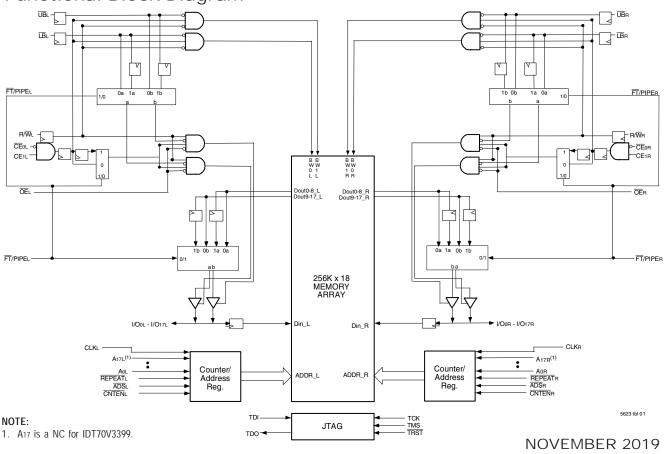
RENESAS

HIGH-SPEED 3.3V 256/128K x 18 **SYNCHRONOUS DUAL-PORT STATIC RAM** WITH 3.3V OR 2.5V INTERFACE

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access
 - Commercial: 3.6ns (166MHz)/4.2ns (133MHz) (max.)
 - Industrial: 4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
 - Due to limited pin count PL/FT option is not supported on the 128-pin TQFP package. Device is pipelined outputs only on each port.
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 6ns cycle time, 166MHz operation (6Gbps bandwidth)
 - Fast 3.6ns clock to data out
 - 1.7ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 166MHz
 - Data input, address, byte enable and control registers

- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- Dual Cycle Deselect (DCD) for Pipelined Output mode
- LVTTL- compatible, single 3.3V (±150mV) power supply for core
- ٠ LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- ٠ Industrial temperature range (-40°C to +85°C) is available at 133MHz.
- Available in a 128-pin Thin Quad Flatpack, 208-pin fine pitch Ball Grid Array, and 256-pin Ball **Grid Arrav**
- Supports JTAG features compliant to IEEE 1149.1
 - Due to limited pin count, JTAG is not supported on the 128-pin TQFP package
- Green parts available, see ordering information



Functional Block Diagram

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

5623 drw 02c

Description:

The IDT70V3319/99 is a high-speed 256/128K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V3319/99 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70V3319/99 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
I/O9L	NC	Vss	TDO	NC	A16L	A12L	Asl	NC	Vdd	CLK∟		A4L	Aol	OPT∟	NC	Vss	A
NC	Vss	NC	TDI	A _{17L} ⁽¹⁾	A13L	A9L	NC	CEOL	Vss	ADSL	A5L	Aıl	Vss	VDDQR	I/O8L	NC	в
VDDQL	I/O9r	VDDQR	PIPE/FTL	NC	A14L	A10L	ŪBL	CE1L	Vss	R/₩∟	A6L	A2L	Vdd	I/O8R	NC	Vss	С
NC	Vss	I/O10L	NC	A15L	A11L	A7L	<u>LB</u> L	Vdd	ŌĒL	REPEAT	. Asl	Vdd	NC	VDDQL	I/O7L	I/O7R	D
I/O11L	NC	Vddqr	I/O10R										I/O6L	NC	Vss	NC	E
VDDQL	I/O11R	NC	Vss										Vss	I/O6r	NC	VDDQR	F
NC	Vss	I/O12L	NC					/3319					NC	VDDQL	I/O5l	NC	G
VDD	NC	VDDQR	I/O12R					F208 G20					Vdd	NC	Vss	I/O5r	н
VDDQL	Vdd	Vss	Vss					08-P					Vss	Vdd	Vss	Vddqr	J
I/O14R	Vss	I/O13R	Vss					pBG <i>i</i> o Vie					I/O3r	Vddql	I/O4r	Vss	К
NC	I/O14L	Vddqr	I/O13L										NC	I/O3L	Vss	I/O4L	L
VDDQL	NC	I/O15R	Vss										Vss	NC	I/O2r	Vddqr	м
NC	Vss	NC	I/O15L										I/O1r	VDDQL	NC	I/O2L	N
I/O16R	I/O16L	Vddqr	NC	TRST	A16R	A12R	Авя	NC	Vdd	CLKR	ONTEN I	A4R	NC	I/O1L	Vss	NC	Р
Vss	NC	I/O17R	тск	A _{17R} (1)	A13R	A9R	NC	CEOR	Vss	ADSR	A5R	A1R	Vss	Vddql	I/Oor	VDDQR	R
NC	I/O17L	Vddql	TMS	NC	A14R	A10R	ŪBR	CE1R	Vss	R/WR	Agr	A2R	Vss	NC	Vss	NC	Т
Vss	NC	PIPE/FTR	NC	A15R	A 11R	A7R	LB R	Vdd	ŌĒr	REPEAT	я Азя	Aor	Vdd	OPTR	NC	I/Ool	U

Pin Configuration^(1,2,3,4,5)

NOTES:

1. A17 is a NC for IDT70V3399.

- 2. All VDD pins must be connected to 3.3V power supply.
- 3. All VDDO pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 4. All Vss pins must be connected to ground supply.
- 5. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 6. This package code is used to reference the package diagram.
- 7. This text does not indicate orientation of the actual part-marking.

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Pin Configuration^(1,2,3,4,5) (con't.)

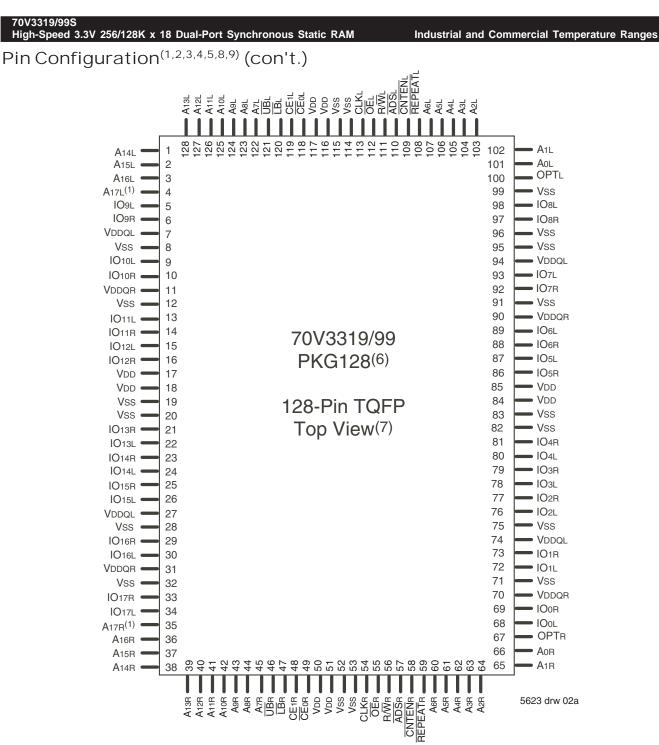
70V3319/99 BC256⁽⁶⁾ BCG256⁽⁶⁾

256-Pin BGA Top View⁽⁷⁾

A1	^{A2}	A3	A4	A5	A6	A7	A8	A9	OEL	A11	A12	A13	A14	A15	A16
NC	TDI	NC	A17L ⁽¹⁾	A14L	A11L	A8L	NC	CE1L		CNTENL	A 5L	A 2L	A0L	NC	NC
B1 NC	^{B2} NC	^{B3} TDO	^{B4} NC	B5 A15L	B6 A12L	B7 A9L	B8 UBl	B9 CE0L	B10 R/WL	B 1 1 REPEATL	B12 A4L	B13 A1L	B14 Vdd	B15 NC	^{B16} NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
NC	I/O9L	Vss	A16L	A13L	A10L	A7L	NC	LBL	CLKL	ADSL	A6L	A3L	OPT∟	NC	I/O8L
D1	d2	D3	D4	d5	d6	d7	d8	d9	d10	d11	d12	D13	D14	D15	d16
NC	I/O9r	NC	PIPE/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	NC	NC	I/O8r
e1	e2	E3	e4	e5	e6	e7	E8	^{E9}	E10	e11	e12	e13	E14	e15	e16
I/O10r	I/O10L	NC	Vddql	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddqr	NC	I/O7l	I/O7r
f1	F2	f3	f4	f5	F6	^{F7}	F8	^{F9}	F10	F11	F12	f13	f14	F15	F16
I/O11L	NC	I/O11R	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O6r	NC	I/O6L
G1	G2	G3	g4	G5	G6	G7	G8	^{G9}	G10	G11	G12	G13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	VSS	Vddql	I/O5L	NC	NC
H1	h2	H3	h4	H5	H6	H7	H8	H9	H10	H11	H12	h13	H14	H15	h16
NC	I/O12R	NC	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	NC	NC	I/O5r
J1	j2	j3	j4	_{J5}	^{J6}	_{J7}	_{J8}	^{J9}	J10	J11	J12	j13	J14	j15	J16
I/O13L	I/O14R	I/O13R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O4r	I/O3r	I/O4L
K1	K2	k3	k4	^{K5}	K6	к7	K8	к9	K10	K11	K12	k13	K14	K15	к16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	NC	NC	I/Oзl
l1	L2	l3	l4	l5	L6	L7	L8	L9	L10	L11	l12	l13	l14	L15	l16
I/O15L	NC	I/O15R	Vddqr	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O2l	NC	I/O2R
M1		M3	^{m4}	^{M5}	M6	M7	^{M8}	M9	M10	M11	M12	m13	м14	M15	M16
I/O16R		NC	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O1r	I/O1L	NC
N1	n2	N3	N4	ⁿ⁵	ⁿ⁶	n7	n8	^{N9}	n10	N11	n12	N13	N14	n15	N16
NC	I/O17r	NC	PIPE/FTR	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	NC	I/Oor	NC
P1	Р2	P3	P4	P5	P6	P7	P8	P9	P10	^{P11}	P12	P13	P14	P15	P16
NC	I/O17L	TMS	A16R	A13R	A10R	A7R	NC	LBr	CLKR	ADSr	A 6R	A3R	NC	NC	I/Ool
^{R1}	^{R2}	^{R3}	^{R4}	R5	R6	R7	r8	R9	r10	r11		R13	^{R14}	^{R15}	R16
NC	NC	TRST	NC	A15R	A12R	A 9R	UBr	CE0R	R/Wr	REPEATR		A 1R	OPTr	NC	NC
T1	T2	тз	T4	T5	T6	t7	T8	^{T9}	T10	t11	T12	T13	T14	T15	^{T16}
NC	TCK	NC	A 17R ⁽¹⁾	A 14R	A11R	A8r	NC	CE1R	OEr	CNTENR	A 5R	A 2R	Aor	NC	NC

5623 drw 02d

- 1. A17 is a NC for IDT70V3399.
- 2. All VDD pins must be connected to 3.3V power supply.
- 3. All VDDO pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 4. All Vss pins must be connected to ground supply.
- 5. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 6. This package code is used to reference the package diagram.
- 7. This text does not indicate orientation of the actual part-marking.



NOTES:

- 1. A17 is a NC for IDT70V3399.
- 2. All VDD pins must be connected to 3.3V power supply.

3. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).

- $\label{eq:alpha} \text{All Vss pins must be connected to ground supply.}$
- 5. Package body is approximately 14mm x 20mm x 1.4mm.
- 6. This package code is used to reference the package diagram.
- 7. This text does not indicate orientation of the actual part-marking.
- 8. PIPE/FT option in PKG128 is not supported due to limitation in pin count. Device is pipelined outputs only on each port.
- 9. Due to the limited pin count, JTAG is not supported in the PKG128 package.

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Pin Names

Left Port	Right Port	Names	
ŒUL, CE1L	CEOR, CE1R	Chip Enables ⁽⁶⁾	
R/WL	R/WR	Read/Write Enable	
OEL	ŌĒr	Output Enable	
Aol - A17l ⁽¹⁾	Aor - A17r ⁽¹⁾	Address	
1/Ool - 1/O17L	1/O0r - 1/017r	Data Input/Output	
CLKL	CLKr	Clock	
PIPE/FTL ⁽⁵⁾	PIPE/FTR ⁽⁵⁾	Pipeline/Flow-Through	
ADSL	ADS _R	Address Strobe Enable	
<u>CNTEN</u> L		Counter Enable	
REPEATL		Counter Repeat ⁽⁴⁾	
ŪBL	UB R	Upper Byte Enable (I/O9-I/O17) ⁽⁶⁾	
LB L	LB R	Lower Byte Enable (I/Oo-I/O8) ⁽⁶⁾	
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽²⁾	
OPTL	OPTR	Option for selecting VDDQX ^(2,3)	1.
	Vdd	Power (3.3V) ⁽²⁾	2.
	Vss	Ground (0V)	3.
	TDI	Test Data Input	
	TDO	Test Data Output	
	TCK	Test Logic Clock (10MHz)	
	TMS	Test Mode Select	4.
	TRST	Reset (Initialize TAP Controller)	5.

I. A17 is a NC for IDT70V3399.

- VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 3. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDOX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and address controls will operate at 2.5V levels and VDDOX must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

 When REPEATx is asserted, the counter will reset to the last valid address loaded via ADSx.

 PIPE/FT option in PK-128 package is not supported due to limitation in pin count. Device is pipelined output mode only on each port.

 Chip Enables and Byte Enables are double buffered when PL/FT = ViH, i.e., the signals take two cycles to deselect.

5623 tbl 01

Industrial and Commercial Temperature Ranges

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Ē€	CE1	ŪB	LB	R/W	Upper Byte I/O9-17	Lower Byte I/Oo-8	MODE
Х	Ŷ	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	Ŷ	Х	L	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	Ŷ	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	Ŷ	L	Н	Н	L	L	High-Z	Din	Write to Lower Byte Only
Х	Ŷ	L	Н	L	Н	L	Din	High-Z	Write to Upper Byte Only
Х	Ŷ	L	Н	L	L	L	Din	Din	Write to Both Bytes
L	Ŷ	L	Н	Н	L	Н	High-Z	Dout	Read Lower Byte Only
L	Ŷ	L	Н	L	Н	Н	Dout	High-Z	Read Upper Byte Only
L	Ŷ	L	Н	L	L	Н	Dout	Dout	Read Both Bytes
Н	Ŷ	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$.

3. OE is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2)

External Address	Previous Internal Address	Internal Address Used	CLK	ADS	CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
Х	Х	An	Ŷ	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to last valid ADS load
An	Х	An	Ŷ	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
An	Ар	Ар	Ŷ	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	Ŷ	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation
NOTES								5623 tbl 03

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CE0, CE1, UB, LB and OE.

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the date out will be delayed by one cycle.

4. ADS and REPEAT are independent of all other memory control signals including CE0, CE1 and UB, LB.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, UB, LB.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

5623 tbl 02

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV
	•		5623 tbl 04

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias ⁽³⁾	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
ЛІЛ	Junction Temperature	+150	٥C
Іоит	DC Output Current	50	mA
			5623 tbl 06

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 150mV.

3. Ambient Temperature Under Bias. No AC Conditions. Chip Deselected.

Industrial and Commercial Temperature Ranges

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	۷
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V
Vss	Ground	0	0	0	۷
Vih	Input High Voltage (Address & Control Inputs)	1.7	-	Vddq + 100mV ⁽²⁾	V
Vih	Input High Voltage - I/O ⁽³⁾	1.7		VDDQ + 100mV ⁽²⁾	V
Vil	Input Low Voltage	-0.3 ⁽¹⁾	_	0.7	V
				56	23 tb I 05a

NOTES:

1. Undershoot of VIL $_{\geq}$ -1.5V for pulse width less than 10ns is allowed.

2. VTERM must not exceed VDDQ + 100mV.

 To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDOX for that port must be supplied as indicated above.

Conc	litions with V	DDQ	at	3.3V	
Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	۷
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	۷
Vss	Ground	0	0	0	۷
Vih	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	V
Vih	Input High Voltage - I/O ⁽³⁾	2.0	_	VDDQ + 150mV ⁽²⁾	V
VIL	Input Low Voltage	-0.3(1)		0.8	V

Recommended DC Operating Conditions with VDDQ at 3.3V

NOTES:

1. Undershoot of VIL \geq -1.5V for pulse width less than 10ns is allowed.

2. VTERM must not exceed VDDQ + 150mV.

3. To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDox for that port must be supplied as indicated above.

5623 tbl 05b

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

5623 tbl 08

Symbol	Parameter	Conditions ⁽²⁾	Мах.	Unit
Cin	Input Capacitance	VIN = 3dV	8	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF

Capacitance⁽¹⁾(TA = +25°C, F = 1.0MHz)

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

			70V33	19/99S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	$V_{DDQ} = Max., V_{IN} = 0V$ to V_{DDQ}		10	μA
ILO	Output Leakage Currentt ⁽¹⁾	\overline{CE}_0 = Vih or CE1 = Vil, Vout = 0V to VDDQ		10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, $VDDQ = Min$.		0.4	V
Voн (3.3V)	Output High Voltage ⁽²⁾	Ioh = -4mA, VDDQ = Min.	2.4		V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, $VDDQ = Min$.		0.4	V
Voн (2.5V)	Output High Voltage ⁽²⁾	Ioh = -2mA, VDDQ = Min.	2.0		V

5623 tbl 07

NOTE:

1. At VDD \leq 2.0V leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($V_{DD} = 3.3V \pm 150 \text{mV}$)

				70V3319/99S16 Com'l Only Version Typ. ⁽⁴⁾ Max.			Co	9/99S133 m'l Ind	
Symbol	Parameter	Test Condition	Versio			Мах.	Тур. ⁽⁴⁾	Мах.	Unit
IDD	Dynamic Operating	\overline{CE}_{L} and $\overline{CE}_{R} = VIL$,	COM'L	S	370	500	320	400	mA
	Current (Both Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S			320	480	1
ISB1	Standby Current	$\overline{CEL} = \overline{CER} = VH,$	COM'L	S	125	200	115	160	mA
	(Both Ports - TTL Level Inputs)	Outputs Disabled, $f = fMAX^{(1)}$	IND	S			115	195]
ISB2	Standby Current	CE"A" = VIL and CE"B" = VIH ⁽⁵⁾	COM'L	S	250	350	220	290	mA
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S			220	350	
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports Outputs Disabled \overline{CEL} and $\overline{CER} \ge VDDQ - 0.2V$,	COM'L	S	15	30	15	30	mA
	Level Inputs)	$ \begin{array}{l} \text{VIN} \geq \text{VDDQ} & -0.2\text{V} \\ \text{or} \text{ VIN} \leq 0.2\text{V}, \ \text{f} = 0^{(2)} \end{array} $	IND	S			15	40	
ISB4	Full Standby Current (One Port - CMOS	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDDQ - 0.2V^{(5)}$	COM'L	S	250	350	220	290	mA
	Level Inputs)	$VIN \ge VDDQ - 0.2V$ or $VIN \le 0.2V$ Active Port, Outputs Disabled, f = fMAX ⁽¹⁾	IND	S		_	220	350	
OTES.								56	23 tbl

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. VDD = 3.3V, TA = $25^{\circ}C$ for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).

5. $\overline{CEx} = VIL$ means $\overline{CEox} = VIL$ and CE1x = VIH $\overline{CEx} = VIH$ means $\overline{CEox} = VIH$ or CE1x = VIH

 $\overline{CE}x \leq 0.2V$ means $\overline{CE}\textsc{ox} \leq 0.2V$ and CE1x \geq VDDQ - 0.2V

 $\overline{CE}x \ge VDDQ$ - 0.2V means $\overline{CE}ox \ge VDDQ$ - 0.2V or CE1x - 0.2V

"X" represents "L" for left port or "R" for right port.

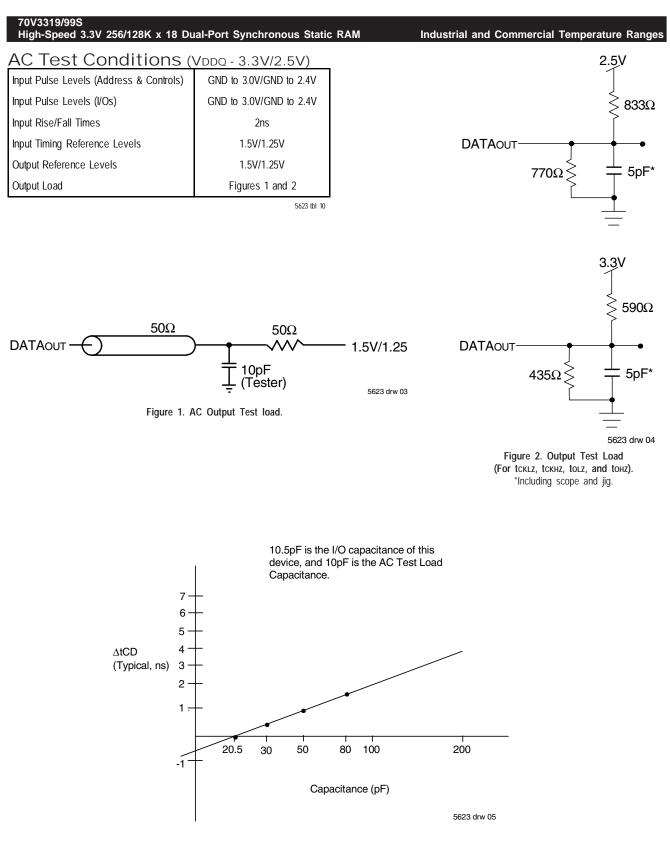


Figure 3. Typical Output Derating (Lumped Capacitive Load).

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)^(2,3) (V_{DD} = $3.3V \pm 150$ mV, T_A = 0°C to +70°C)

Symbol			70V3319/99S166 Com'l Only		70V3319/99S133 Com'l & Ind	
	Parameter	Min.	Max.	Min.	Мах.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	20		25		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	6		7.5		ns
tCH1	Clock High Time (Flow-Through) ⁽¹⁾	6		7		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	6		7		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	2.1		2.6		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.1	_	2.6		ns
tsa	Address Setup Time	1.7	_	1.8		ns
tha	Address Hold Time	0.5		0.5		ns
tsc	Chip Enable Setup Time	1.7		1.8		ns
tнc	Chip Enable Hold Time	0.5		0.5		ns
tsв	Byte Enable Setup Time	1.7		1.8		ns
tнв	Byte Enable Hold Time	0.5		0.5		ns
tsw	R/W Setup Time	1.7		1.8		ns
tHW	R/W Hold Time	0.5		0.5		ns
tsp	Input Data Setup Time	1.7		1.8		ns
thd	Input Data Hold Time	0.5		0.5		ns
tsad	ADS Setup Time	1.7		1.8		ns
thad	ADS Hold Time	0.5		0.5		ns
tscn	CNTEN Setup Time	1.7		1.8		ns
then	CNTEN Hold Time	0.5		0.5		ns
İ SRPT	REPEAT Setup Time	1.7		1.8		ns
T HRPT	REPEAT Hold Time	0.5		0.5		ns
toe	Output Enable to Data Valid		4.0		4.2	ns
tolz	Output Enable to Output Low-Z	1		1		ns
tонz	Output Enable to Output High-Z	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾	—	12		15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾	—	3.6		4.2	ns
tDC	Data Output Hold After Clock High	1		1		ns
tскнz	Clock High to Output High-Z	1	3	1	3	ns
tcklz.	Clock High to Output Low-Z	1		1		ns
Port-to-Port D	Jelay	•	-			
tco	Clock-to-Clock Offset	5		6		ns

NOTES:

1. The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when \overline{FT} /PIPEx = VIH. Flow-through parameters (tcvc1, tcb1) apply when \overline{FT} /PIPE = VIL for that port.

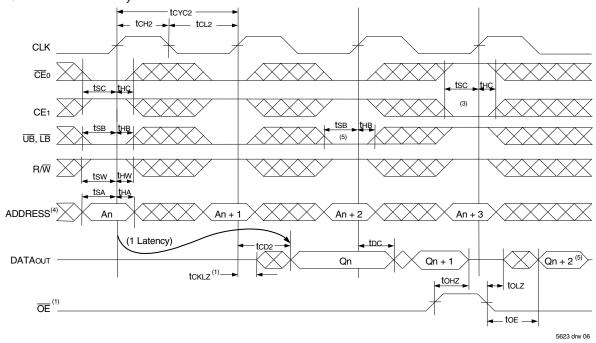
2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

3. These values are valid for either level of VDDQ (3.3V/2.5V). See page 5 for details on selecting the desired operating voltage levels for each port.

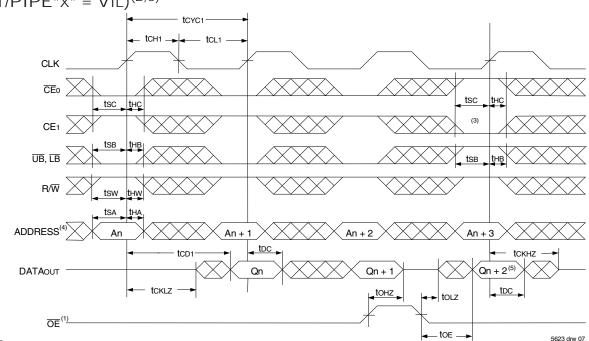
70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges







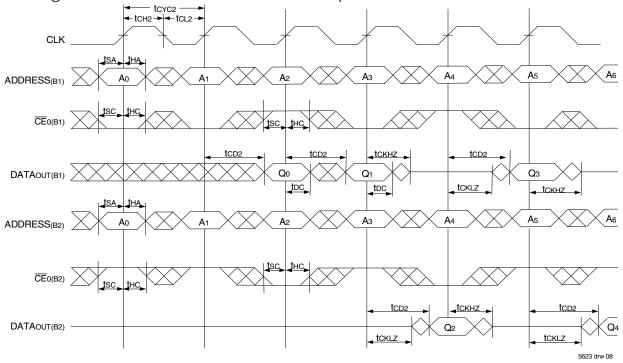


- 1. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 2. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{REPEAT} = VIH$.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, \overline{UB} , $\overline{LB} = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
 are for reference use only.
- 5. If UB, LB was HIGH, then the appropriate Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.

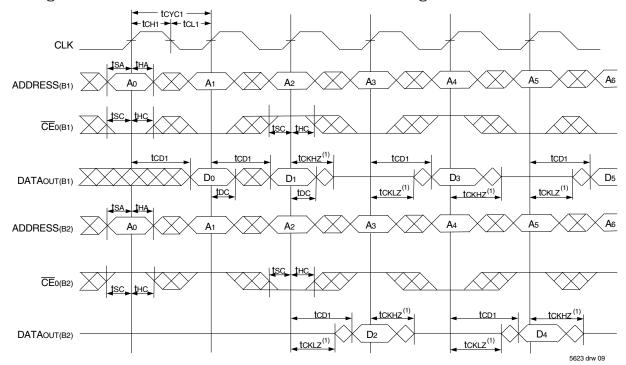
70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of a Multi-Device Pipelined Read^(1,2)



Timing Waveform of a Multi-Device Flow-Through Read^(1,2)

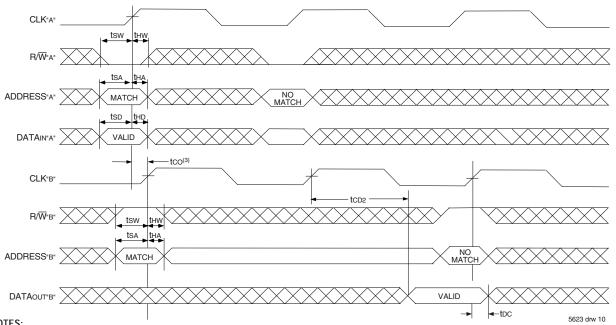


- 1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V3319/99 for this waveform,
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{REPEAT} = VIH.

70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

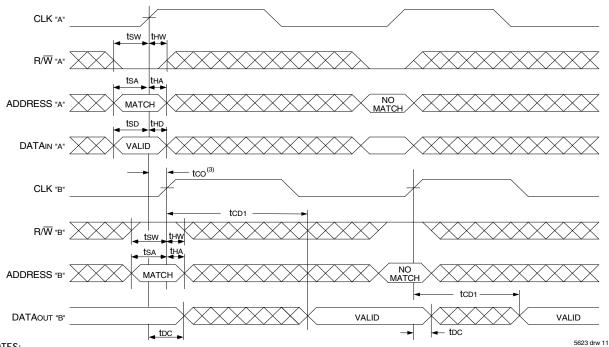
Industrial and Commercial Temperature Ranges

Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2,4)



- NOTES:
- 1. \overline{CE}_{0} , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read^(1,2,4)



NOTES:

1. \overline{CE}_{0} , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.

2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.

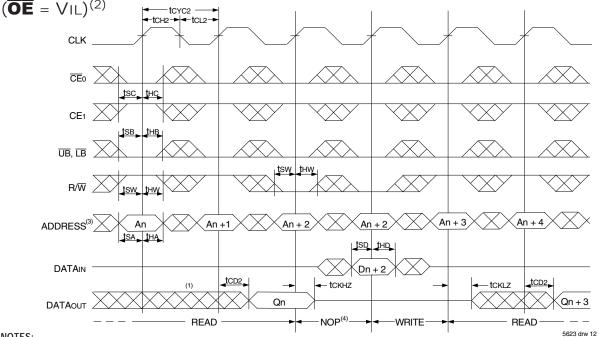
If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc + tcp1). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcp1).

4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

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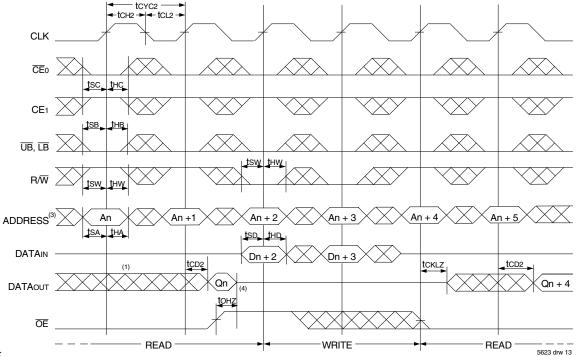
Timing Waveform of Pipelined Read-to-Write-to-Read



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = VIH$. "NOP" is "No Operation".
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾

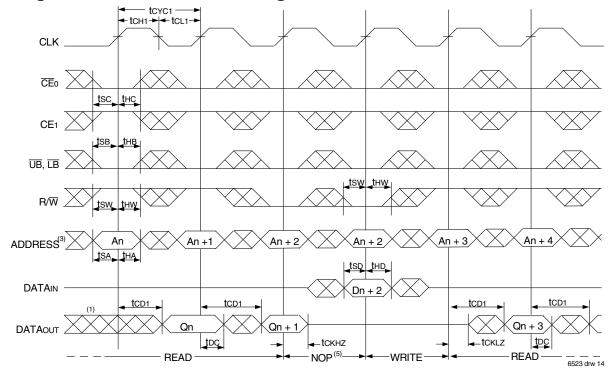


- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

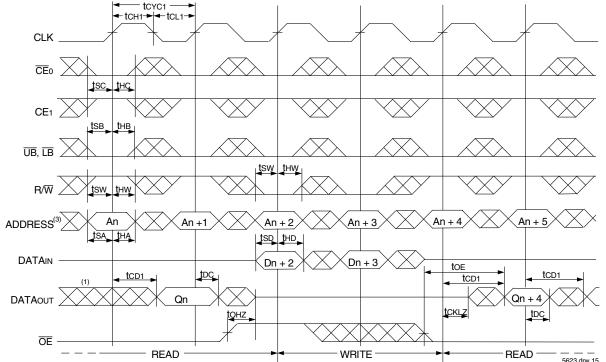
70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽²⁾



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

2. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.

3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

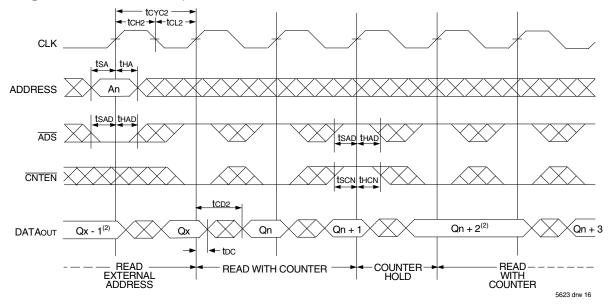
4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.



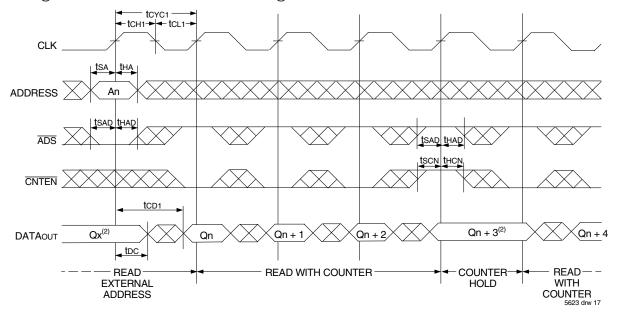
70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾



NOTES:

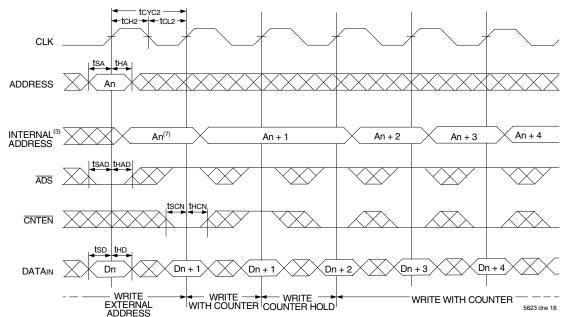
1. \overline{CE}_{0} , \overline{OE} , \overline{UB} , \overline{LB} = VIL; CE1, R/W, and \overline{REPEAT} = VIH.

2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data output remains constant for subsequent clocks.

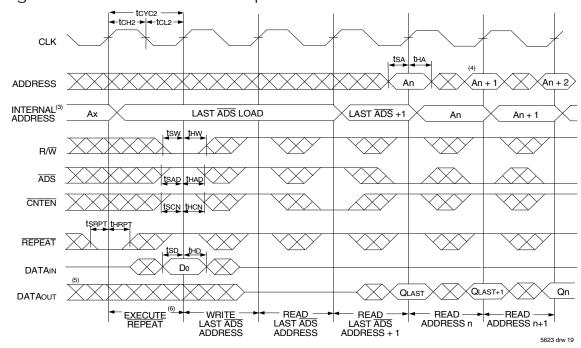
70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾



Timing Waveform of Counter Repeat⁽²⁾



- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE1 and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{CE}_{0} , \overline{UB} , \overline{LB} = VIL; CE_{1} = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. Extra cycles are shown here simply for clarification. For more information on REPEAT function refer to Truth Table II.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.

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Functional Description

The IDT70V3319/99 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

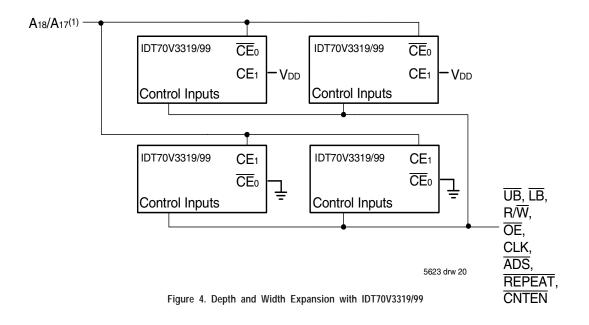
A HIGH on \overline{CE} or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V3319/99s for depth expansion configurations. Two cycles are required with \overline{CE} LOW and CE1 HIGH to reactivate the outputs.

Industrial and Commercial Temperature Ranges

Depth and Width Expansion

The IDT70V3319/99 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V3319/99 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 36-bits or wider.



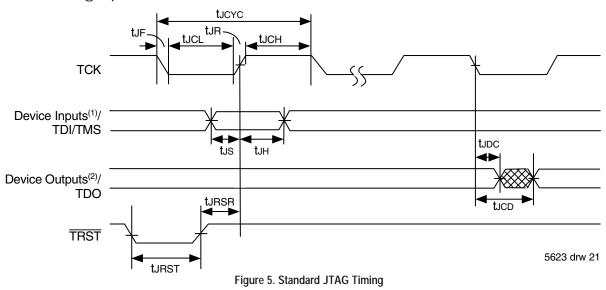
NOTE:

1. A17 is for IDT70V3319, A16 is for IDT70V3399.

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JTAG Timing Specifications



NOTES:

- 1. Device inputs = All device inputs except TDI, TMS, and TRST.
- 2. Device outputs = All device outputs except TDO.

		7	0V3319/9	9
Symbol	Parameter	Min.	Мах.	Units
tucyc	JTAG Clock Input Period	100		ns
рсн	JTAG Clock HIGH	40		ns
U CL	JTAG Clock Low	40		ns
tır	JTAG Clock Rise Time		3(1)	ns
UF	JTAG Clock Fall Time		3(1)	ns
URST	JTAG Reset	50		ns
URSR	JTAG Reset Recovery	50		ns
ticd	JTAG Data Output		25	ns
tudc	JTAG Data Output Hold	0		ns
tıs	JTAG Setup	15		ns
tн	JTAG Hold	15		ns

JTAG AC Electrical Characteristics^(1,2,3,4)

NOTES:

1. Guaranteed by design.

2. 30pF loading on external output signals.

3. Refer to AC Electrical Test Conditions stated earlier in this document.

4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

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Industrial and Commercial Temperature Ranges

Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x0314 ⁽¹⁾	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

NOTE:

1. Device ID for IDT70V3399 is 0x0315.

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5623 tbl 14

System Interface Parameters

Instruction	Code	Description
EXTEST	0000	Forces contents of the bound ary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0011	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

NOTES:

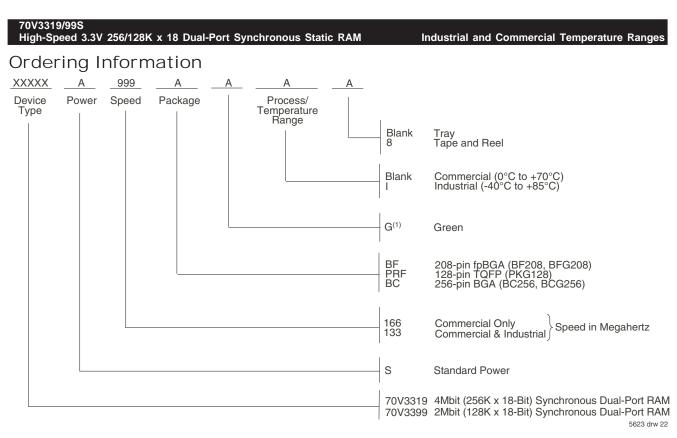
1. Device outputs = All device outputs except TDO.

2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.

3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

5623 tbl 13

5623 tbl 15



NOTES:

 Contact your local sales office for industrial temp. range for other speeds, packages and powers. LEAD FINISH (SnPb) parts are Obsolete excluding BGA & fpBGA. Product Discontinuation Notice - PDN# SP-17-02 Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70V3319S133BC	BC256	CABGA	С
	70V3319S133BC8	BC256	CABGA	С
	70V3319S133BCGI	BCG256	CABGA	Ι
	70V3319S133BCI	BC256	CABGA	I
	70V3319S133BCl8	BC256	CABGA	I
	70V3319S133BF	BF208	CABGA	С
	70V3319S133BF8	BF208	CABGA	С
	70V3319S133BFI	BF208	CABGA	I
	70V3319S133BFI8	BF208	CABGA	I
	70V3319S133PRFGI	PKG128	TQFP	I
	70V3319S133PRFGI8	PKG128	TQFP	I
166	70V3319S166BC	BC256	CABGA	С
	70V3319S166BC8	BC256	CABGA	С
	70V3319S166BCG	BCG256	CABGA	С
	70V3319S166BF	BF208	CABGA	С
	70V3319S166BF8	BF208	CABGA	С
	70V3319S166BFG	BFG208	CABGA	С
	70V3319S166BFG8	BFG208	CABGA	С
	70V3319S166PRFG	PKG128	TQFP	С
	70V3319S166PRFG8	PKG128	TQFP	С

Orderable Part Information

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70V3399S133BC	BC256	CABGA	С
	70V3399S133BC8	BC256	CABGA	С
	70V3399S133BCI	BC256	CABGA	I
	70V3399S133BCI8	BC256	CABGA	I
	70V3399S133BF	BF208	CABGA	С
	70V3399S133BF8	BF208	CABGA	С
	70V3399S133BFI	BF208	CABGA	I
	70V3399S133BFI8	BF208	CABGA	I
166	70V3399S166BC	BC256	CABGA	С
	70V3399S166BC8	BC256	CABGA	С
	70V3399S166BF	BF208	CABGA	С
	70V3399S166BF8	BF208	CABGA	С
	70V3399S166BFG	BFG208	CABGA	С
	70V3399S166BFG8	BFG208	CABGA	С

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Datasheet Document History:

06/02/00:	Initial Public Offering
07/12/00:	Page 1 Added mux to functional block diagram
06/20/01:	Page 1 Added JTAG information for TQFP package
	Page 4 Corrected TQFP package size
07/30/01:	Page 1 Added PL/FT option
	Page 20 Changed maximum value for JTAG AC Electrical Characteristics for tuch from 20ns to 25ns
	Page 9 Added Industrial Temperature DC Parameters
11/20/01:	Page 2, 3 & 4 Added date revision for pin configurations
	Page 11 Changed to Evalue in AC Electrical Characteristics, please refer to Errata #SMEN-01-05
	Page 1 & 22 Replaced ™ logo with [®] logo
	Page 10 Changed AC Test Conditions Input Rise/Fall Times
08/06/02:	Consolidated multiple devices into one datasheet
	Page 1 & 5 Added DCD capability for Pipelined Outputs
	Page 7 Clarified TBIAS and added TJN
	Page 9 Changed DC Electrical Parameters
	Page 11 Removed Clock Rise & Fall Time from AC Electrical Characteristics Table
	Removed Preliminary status
05/19/03:	Page 11 Added Byte Enable SetupTime & Byte Enable Hold Time to AC Electrical Characteristics Table
	Page 22 Added IDT Clock Solution Table
02/08/06:	Page 1 Added green availability to features
	Page 6 Changed footnote 2 for Truth Table I from ADS, CNTEN, REPEAT = VIH to ADS, CNTEN, REPEAT = X
	Page 22 Added green indicator to ordering information
07/25/08:	Page 9 Corrected a typo in the DC Chars table
01/19/09:	Page 22 Removed "IDT" from orderable part number
10/03/14:	Page 22 Added Tape & Reel to the Ordering Information
06/20/18:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
09/12/19:	Page 2, 3 & 4 Updated package codes
	Page 22 Added Orderable Part Information table and removed IDT Clock Solution table
11/04/19:	Page 22 Corrected "ns" to "MHz" in the header of the Orderable Part Information tables